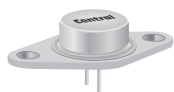


Material Composition Specification

TO-66 Case



Device average mass **5.84 g**
 Fluctuation margin **+/-10%**

Component	Material	Material		Substance	CAS No.	Substance		
		(%wt)	(mg)			(%wt)	(mg)	(ppm)
active device	doped Si	0.07%	4.17	doped Si	7440-21-3	0.07%	4.17	714
die coating*	Slygard 527	0.66%	38.3	Si	--	0.66%	38.3	6,558
bond wire	aluminum	0.02%	1.15	Al	7429-90-5	0.02%	1.15	197
die attach	high temperature solder	0.37%	21.62	Pb	7439-92-1	0.34%	20	3,425
				Sn	7440-31-5	0.02%	1.08	185
				Ag	7440-22-4	0.01%	0.54	92
header	metal alloy	83.4%	4,871	Fe	7439-89-6	82.6%	4,822	825,685
				Ni	7440-02-0	0.83%	48.7	8,339
can	metal alloy	15.48%	904	Fe	7439-89-6	15.3%	895	153,253
				Ni	7440-02-0	0.15%	9	1,541
can plating**	matte tin***	0.001%	0.06	Sn	7440-31-5	0.001%	0.06	9
termination plating**	matte tin***	0.0001%	0.005	Sn	7440-31-5	0.0001%	0.005	1

*Die coating is not used on devices with a V_{CEO} of less than 150 volts.
 **For Lead Free termination plating, add suffix "PB FREE" to part number.
 ***Contact the Central Semiconductor Sales Department for tin/lead plating availability.

Disclaimer
 The information provided in this Material Composition data sheet is, to the best of our knowledge, correct. However, there is no guarantee to completeness or accuracy, as some information is derived from data sources outside the company.

R3 (10-April 2018)